

**SOT-23 Plastic-Encapsulate Transistors****2SC2715** TRANSISTOR (NPN)**FEATURES**

- High Power Gain: $G_{pe}=2\text{dB(Typ.)}(f=10.7\text{MHz})$
- Recommended for FM IF, OSC Stage and AM CONV. IF Stage.

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	35	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
P_C	Collector Power Dissipation	350	mW
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=35\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=12\text{V}, I_C=2\text{mA}$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=1\text{mA}$	100		400	MHz
Power Gain	G_{pe}	$V_{CE}=6\text{V}, I_C=1\text{mA}, f=10.7\text{MHz}$	27		33	dB

CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y
Range	40-80	70-140	120-240
Marking	RR1	RO1	RY1

Typical Characteristics

2SC2715





